

Silicon Variable Capacitance Diode

- For FM tuners
- Monolithic chip with common cathode for perfect tracking of both diodes
- Uniform "square law" characteristics
- Ideal HiFi tuning device when used in low-distortion, back-to-back configuration
- Pb-free (ROHS compliant) package¹⁾
- Qualified according AEC Q101





BB804

BB804



Туре	Package	Configuration	L _S (nH)	Marking
02				

common cathode

Maximum Ratings at $T_A = 25$ °C, unless otherwise specified

SOT23

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_{R}	18	V
Peak reverse voltage	V_{RM}	20	
Forward current	l _F	50	mA
Operating temperature range	T _{op}	-55 12 5	°C
Storage temperature	$T_{\rm stg}$	-55 150	

1

1.8

SF1/2/3*

^{*}For differences see next page Capacitance groups

¹Pb-containing package may be available upon special request



Electrical Characteristics at $T_A = 25$ °C, unless otherwise specified

Parameter	Symbol		Values		
		min.	typ.	max.	
DC Characteristics	•	•			
Reverse current	I _R	-	-		nA
$V_{R} = 16 \text{ V}$		-	-	20	
$V_{R} = 16 \text{ V}, T_{A} = 65 \text{ °C}$				200	
AC Characteristics					
Diode capacitance ¹⁾	C _T	42	-	47.5	pF
$V_{R} = 2 \text{ V}, f = 1 \text{ MHz}$					
Capacitance ratio	C_{T2}/C_{T8}	1.65	1.71	-	
$V_{R} = 2 \text{ V}, V_{R} = 8 \text{ V}, f = 1 \text{ MHz}$					
Series resistance	$r_{\rm S}$	-	0.18	-	Ω
$V_{R} = 2 \text{ V}, f = 100 \text{ MHz}$					
Figure of merit	Q	-	200	-	
$f = 100 \text{ MHz}, V_{R} = 2 \text{ V}$					
Temperature coefficient of diode capacitance	TC _C	-	330	-	ppm/k
$V_{R} = 2 \text{ V}, f = 1 \text{ MHz}$					

 $^{^{\}rm 1}$ Capacitance groups at 2V , coded 1; 2 ; 3

 $C_{\mathrm{T}}/\mathrm{groups}$ 1 2 3 C_{2V} min 43pF 44pF 45pF

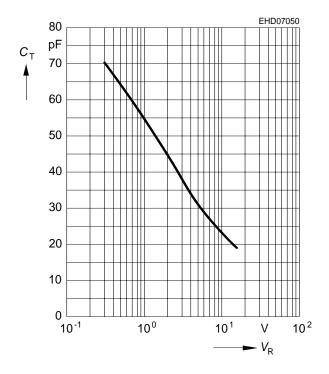
C_{2V} max 44.5pF 45.5pF 46.5pF

The capacitance subgroup is marked by the subgroup number printed on the component and the package label. A packing unit (e.g. 8mm tape) contain diodes of one subgroup only. Delivery of different capacitance subgroups requires a special agreement.

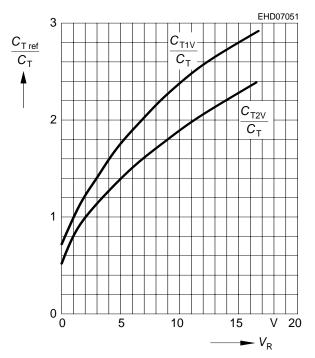


Diode capacitance $C_T = f(V_R)$

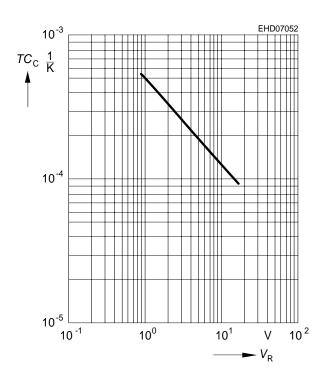
f = 1MHz



Capacitance ratio $C_{\text{Tref}}/C_{\text{T}} = f (V_{\text{R}})$ f = 1 MHz

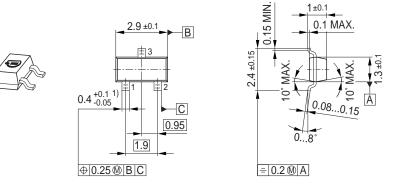


Temperatur coefficient $TC_C = f(V_R)$



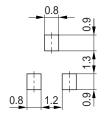


Package Outline

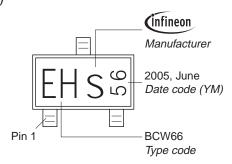


1) Lead width can be 0.6 max. in dambar area

Foot Print

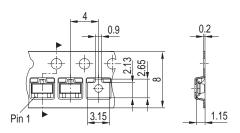


Marking Layout (Example)



Standard Packing

Reel Ø180 mm = 3.000 Pieces/Reel Reel Ø330 mm = 10.000 Pieces/Reel





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